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TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT process)

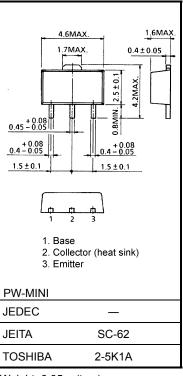
2SA1483

High Frequency Amplifier Applications Video Amplifier Applications High Speed SwitcHing Applications

- High transition frequency: $f_T = 200 \text{ MHz}$ (typ.)
- Low collector output capacitance: $C_{ob} = 3.5 \text{ pF}$ (typ.)
- Complementary to 2SC3803

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	-60	V	
Collector-emitter voltage	V _{CEO}	-45	V	
Emitter-base voltage	V _{EBO}	-5	V	
Continuous collector current	Ι _C	-200	mA	
Continuous base current	Ι _Β	-50	mA	
Collector power dissipation	P _C	500	mW	
	P _C	1000		
	(Note 1)	1000		
Junction temperature	Тј	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	

Absolute Maximum Ratings (Ta = 25°C)



Weight: 0.05 g (typ.)

Note 1: Mounted on a ceramic substrate (250 $\text{mm}^2 \times 0.8 \text{ t}$)

Note 2: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

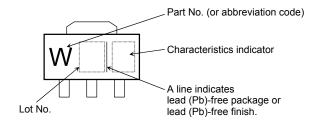
Unit: mm

Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current I _{CBO}		I _{CBO}	V _{CB} = -45 V, I _E = 0	-	—	-0.1	μA
Emitter cut-off current I _{EBO}		I _{EBO}	$V_{EB} = -5 V, I_C = 0$		_	-0.1	μA
DC current gain hFE (1) (Note 3 hFE (2)		h _{FE (1)} (Note 3)	V _{CE} = -1 V, I _C = -10 mA	40	_	240	
		h _{FE (2)}	$V_{CE} = -3 V$, $I_{C} = -200 mA$	20	_	—	
Collector-emitter	saturation voltage	V _{CE (sat)}	I _C = -100 mA, I _B = -10 mA	_	-	-0.3	V
Base-emitter saturation voltage		V _{BE (sat)}	I _C = -100 mA, I _B = -10 mA	—	-	-1.0	V
Transition frequency		fT	$V_{CE} = -10 \text{ V}, I_C = -10 \text{ mA}$	100	200	—	MHz
Input impedance (real part) R		Re (h _{ie})	V_{CE} = -10 V, I _E = 10 mA, f = 200 MHz	—	-	120	Ω
Collector output capacitance		C _{ob}	V_{CB} = -10 V, I _E = 0, f = 1 MHz	_	3.5	5	pF
Switching time	Turn-on time	t _{on}	OUTPUT INPUT 680 Ω 0 -10 $1 \mu s$ V_{BB} = -12 V = 3 V DUTY CYCLE $\leq 2\%$	_	40	_	
	Storage time	t _{stg}		_	250	_	ns
	Fall time	t _f		_	30	_	

Note 3: hFE (1) classification R: 40 to 80, O: 70 to 140, Y: 120 to 240

Marking



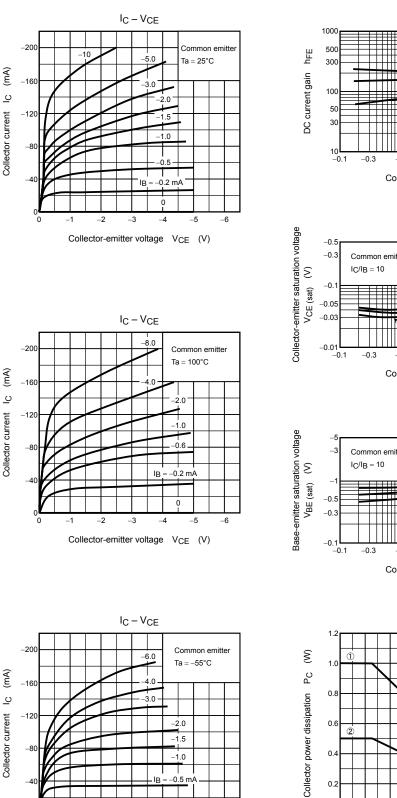
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Common emitter

VCE = -3 V

-30

-100



-1.5

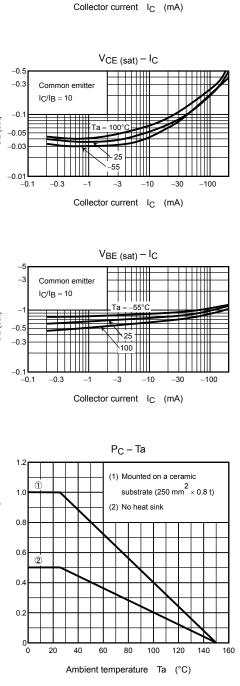
-1.0 -0.5 n IB

0

-5

-6

-4



h_{FE} – I_C

Ta = 100°C

-55

-3

-1

25

-10

-8

0

-1

-2

-3

Collector-emitter voltage VCE (V)

3

RESTRICTIONS ON PRODUCT USE

20070701-EN

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